

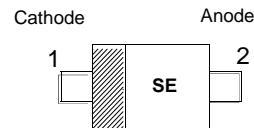


迈拓电子  
MAITUO ELECTRONIC

## MBR0530 Surface Mount Schottky Barrier Diode



- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance
- Also Available in Lead Free Version



Marking Code: **SE**

SOD-123

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	30	V
Non-Repetitive Peak Reverse Voltage	$V_{RSM}$	30	V
Maximum DC Blocking Voltage	$V_R$	30	V
Average Forward Rectified Current	$I_{F(AV)}$	0.5	A
Peak Forward Surge Current (8.3 ms Single Half Sine-wave)	$I_{FSM}$	5.5	A
Thermal Resistance Junction to Lead	$R_{\theta JL}$	150	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction to Ambient <sup>1)</sup>	$R_{\theta JA}$	206	$^\circ\text{C}/\text{W}$
Operating Junction Temperature	$T_j$	- 65 to + 125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 125	$^\circ\text{C}$

<sup>1)</sup> 1 inch square pad size (1 X 0.5 inch for each lead) on FR4 board

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100 \text{ mA}$ at $I_F = 500 \text{ mA}$	$V_F$	0.375 0.5	V
Reverse Current at $V_R = 30 \text{ V}$ at $V_R = 15 \text{ V}$	$I_R$	130 20	$\mu\text{A}$



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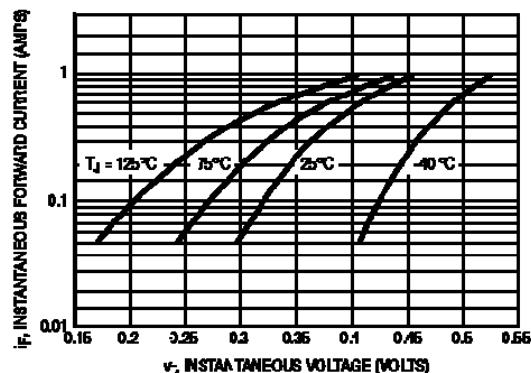


Figure 1. Typical Forward Voltage

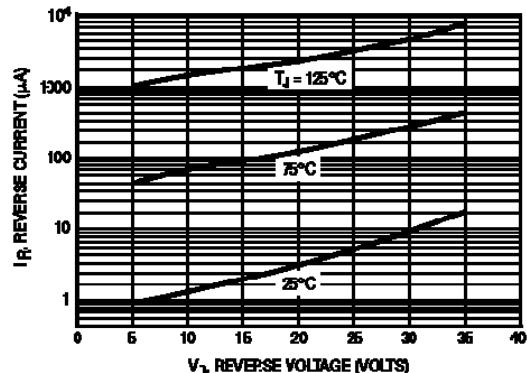


Figure 2. Typical Reverse Current

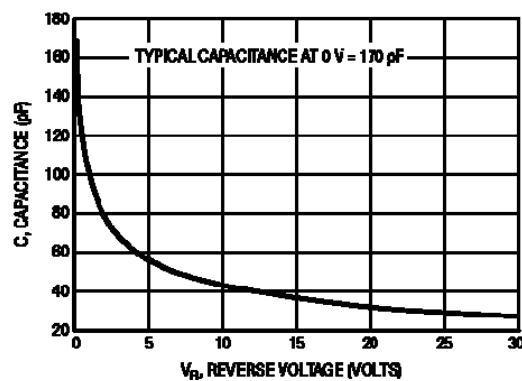


Figure 3. Typical Capacitance

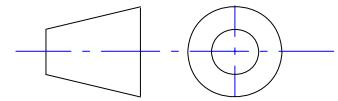
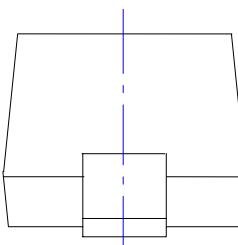
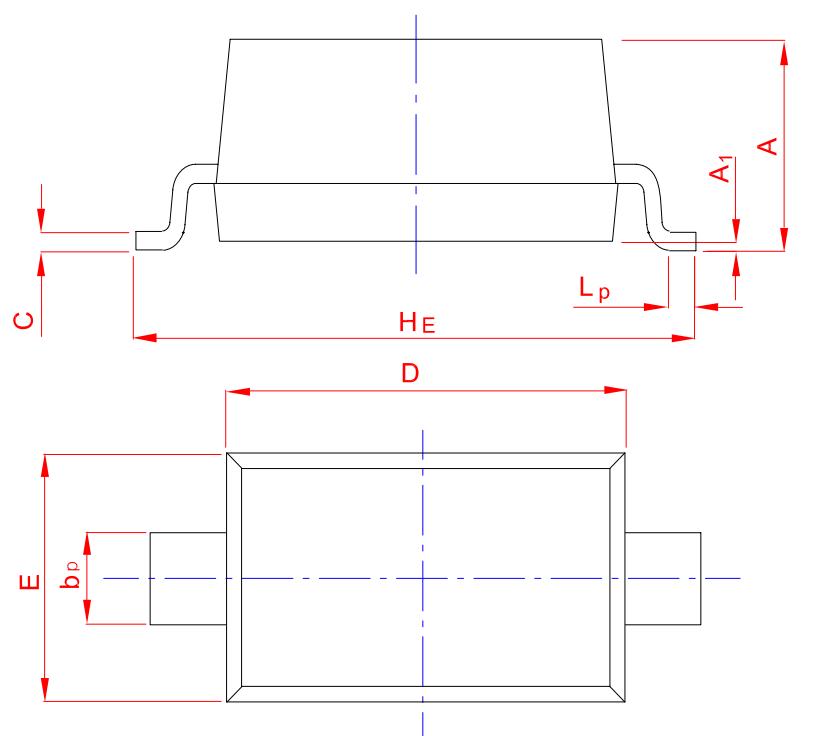


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## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

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UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20